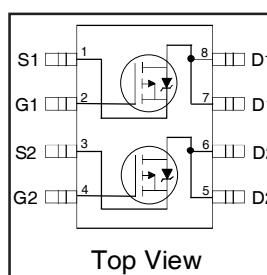


AUIRF7316Q

HEXFET® Power MOSFET

Features

- Advanced Planar Technology
- Low On-Resistance
- Dual P Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- 150°C Operating Temperature
- Automotive [Q101] Qualified
- Lead-Free, RoHS Compliant

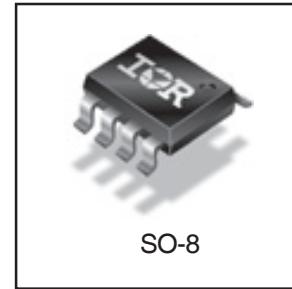


$V_{(BR)DSS}$	-30V
$R_{DS(on)}$ typ.	0.042Ω
max.	0.058Ω
I_D	-4.9A

Description

Specifically designed for Automotive applications, these HEXFET® Power MOSFET's in a Dual SO-8 package utilize the lastest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of these Automotive qualified HEXFET Power MOSFET's are a 150°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These benefits combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.

The efficient SO-8 package provides enhanced thermal characteristics and dual MOSFET die capability making it ideal in a variety of power applications. This dual, surface mount SO-8 can dramatically reduce board space and is also available in Tape & Reel.



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	-30	V
I_D @ $T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ ⑤	-4.9	A
I_D @ $T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ ⑤	-3.9	
I_{DM}	Pulsed Drain Current ①	-30	
I_S	Continuous Source Current (Diode Conduction)	-2.5	
P_D @ $T_A = 25^\circ\text{C}$	Power Dissipation ⑤	2.0	W
P_D @ $T_A = 70^\circ\text{C}$	Power Dissipation ⑤	1.3	
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy	140	mJ
I_{AR}	Avalanche Current	-2.8	A
E_{AR}	Repetitive Avalanche Energy	0.20	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Max.	Units
R_{0JA}	Junction-to-Ambient ⑤	62.5	°C/W

HEXFET® is a registered trademark of International Rectifier.

*Qualification standards can be found at <http://www.irf.com/>

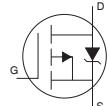
Static Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(\text{BR})\text{DSS}}$	Drain-to-Source Breakdown Voltage	-30	—	—	V	$V_{GS} = 0V, I_D = -250\mu\text{A}$
$\Delta V_{(\text{BR})\text{DSS}}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.022	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = -1\text{mA}$
$R_{DS(\text{on})}$	Static Drain-to-Source On-Resistance	—	0.042	0.058	Ω	$V_{GS} = -10V, I_D = -4.9\text{A}$ ④
		—	0.076	0.098		$V_{GS} = -4.5V, I_D = -3.6\text{A}$ ④
$V_{GS(\text{th})}$	Gate Threshold Voltage	-1.0	—	-3.0	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
g_{fs}	Forward Transconductance	—	7.7	—	S	$V_{DS} = -15V, I_D = -4.9\text{A}$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	$V_{DS} = -24V, V_{GS} = 0V$
		—	—	-25		$V_{DS} = -24V, V_{GS} = 0V, T_J = 55^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = 20V$

Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge	—	23	34	nC	$I_D = -4.9\text{A}$
Q_{gs}	Gate-to-Source Charge	—	3.8	5.7		$V_{DS} = -15V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	5.9	8.9		$V_{GS} = -10V$, See Fig.10 ④
$t_{d(on)}$	Turn-On Delay Time	—	13	19	ns	$V_{DD} = -15V$
t_r	Rise Time	—	13	20		$I_D = -1.0\text{A}$
$t_{d(off)}$	Turn-Off Delay Time	—	34	51		$R_G = 6.0\Omega$
t_f	Fall Time	—	32	48		$R_D = 15\Omega$ ④
C_{iss}	Input Capacitance	—	710	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	380	—		$V_{DS} = -25V$
C_{rss}	Reverse Transfer Capacitance	—	180	—		$f = 1.0\text{MHz}$, See Fig.5

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_s	Continuous Source Current (Body Diode)	—	—	-2.5	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-30		
V_{SD}	Diode Forward Voltage	—	-0.78	-1.0		$T_J = 25^\circ\text{C}, I_s = -1.7\text{A}, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	44	66	ns	$T_J = 25^\circ\text{C}, I_F = -1.7\text{A}$
Q_{rr}	Reverse Recovery Charge	—	42	63	nC	$dI/dt = 100\text{A}/\mu\text{s}$ ④

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting $T_J = 25^\circ\text{C}$, $L = 35\text{mH}$, $R_G = 25\Omega$, $I_{AS} = -2.8\text{A}$.
- ③ $I_{SD} \leq -2.8\text{A}$, $di/dt \leq 150\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(\text{BR})\text{DSS}}$, $T_J \leq 150^\circ\text{C}$
- ④ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
- ⑤ Surface mounted on FR-4 board, $t \leq 10\text{sec}$.

Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101) ^{††}	
Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.			
Moisture Sensitivity Level		SO-8	MSL1
ESD	Machine Model	Class M2(+/- 200V) ^{†††} (per AEC-Q101-002)	
	Human Body Model	Class H1A(+/- 500V) ^{†††} (per AEC-Q101-001)	
	Charged Device Model	Class C5(+/- 2000V) ^{†††} (per AEC-Q101-005)	
RoHS Compliant		Yes	

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

^{††} Exceptions (if any) to AEC-Q101 requirements are noted in the qualification report.

^{†††} Highest passing voltage

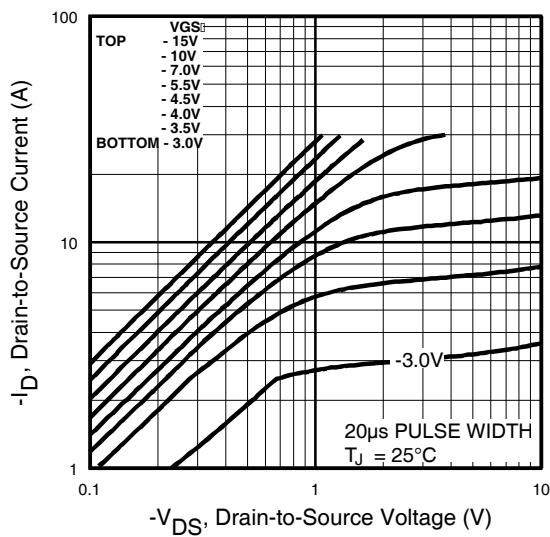


Fig 1. Typical Output Characteristics

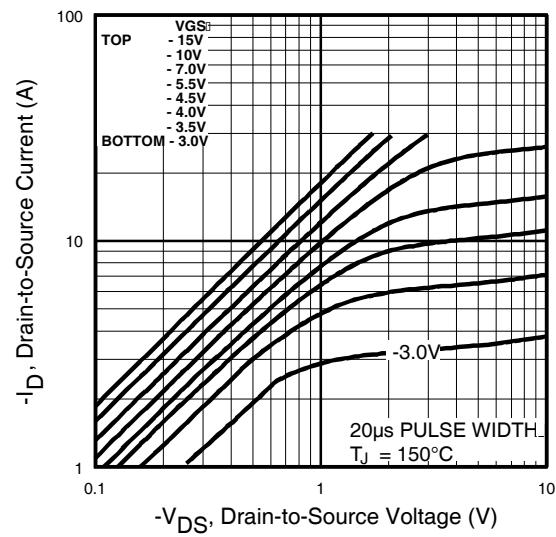


Fig 2. Typical Output Characteristics

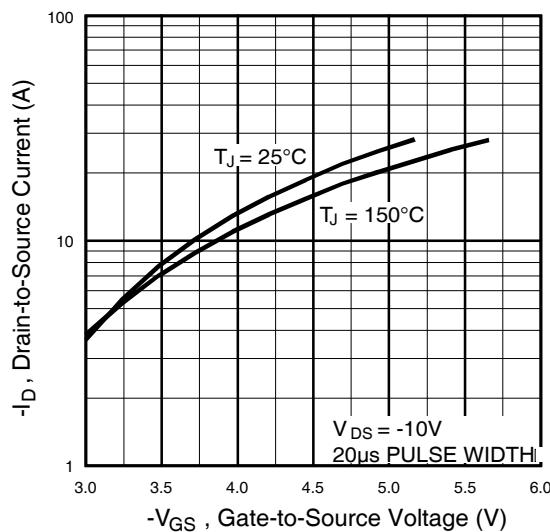


Fig 3. Typical Transfer Characteristics

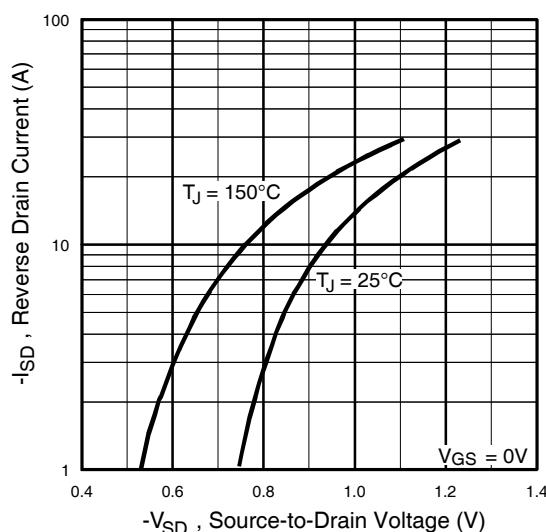


Fig 4. Typical Source-Drain Diode Forward Voltage

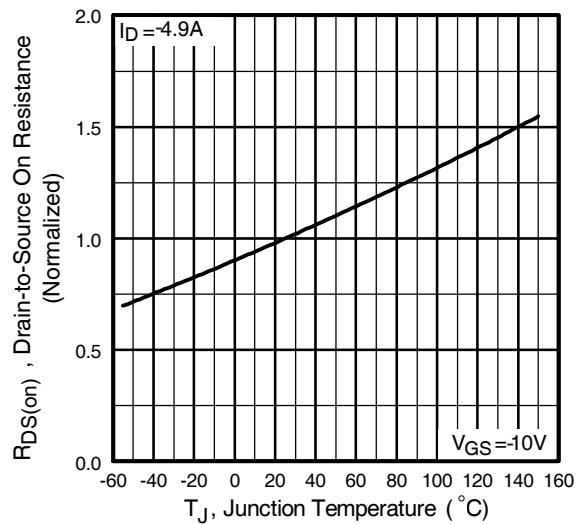


Fig 5. Normalized On-Resistance Vs. Temperature

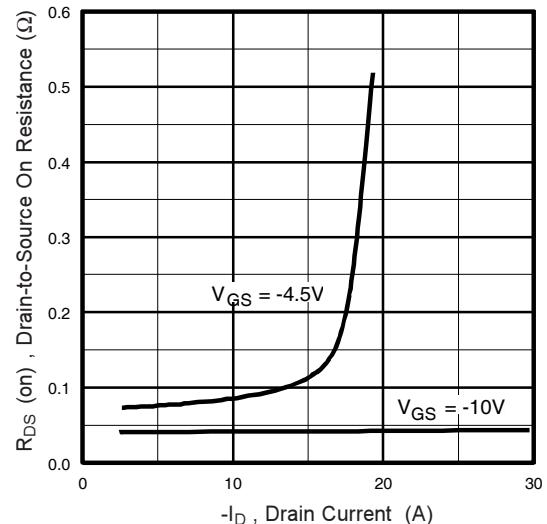


Fig 6. Typical On-Resistance Vs. Drain Current

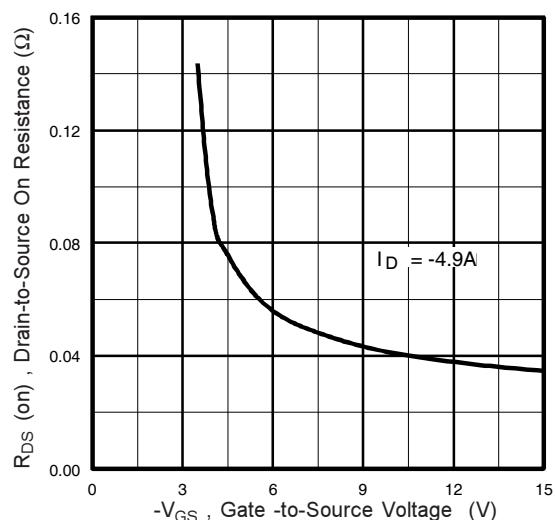


Fig 7. Typical On-Resistance Vs. Gate Voltage

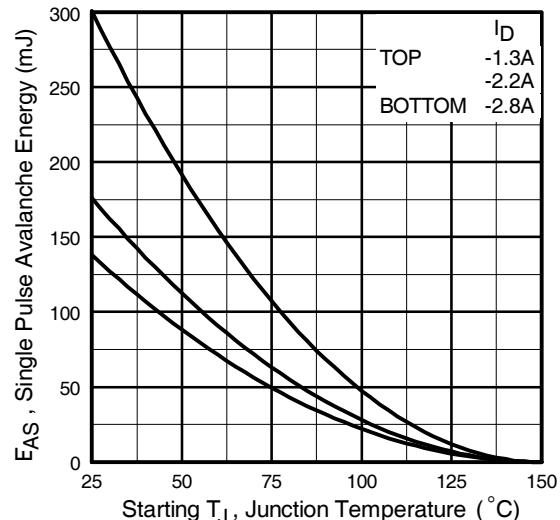


Fig 8. Maximum Avalanche Energy Vs. Drain Current

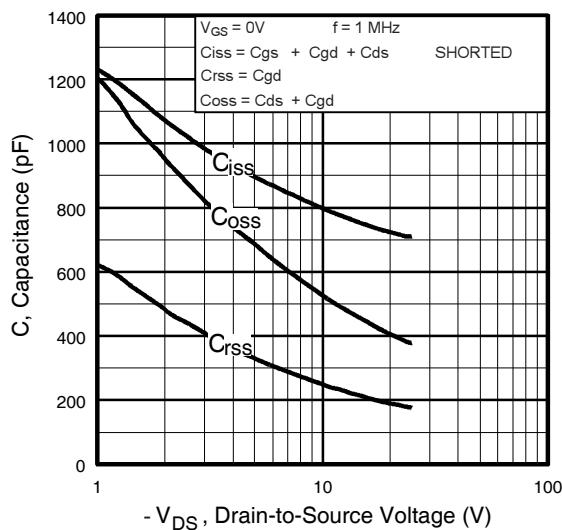


Fig 9. Typical Capacitance Vs.
Drain-to-Source Voltage

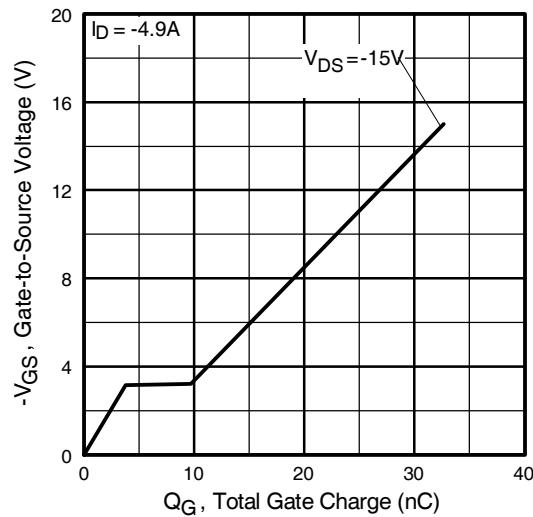


Fig 10. Typical Gate Charge Vs.
Gate-to-Source Voltage

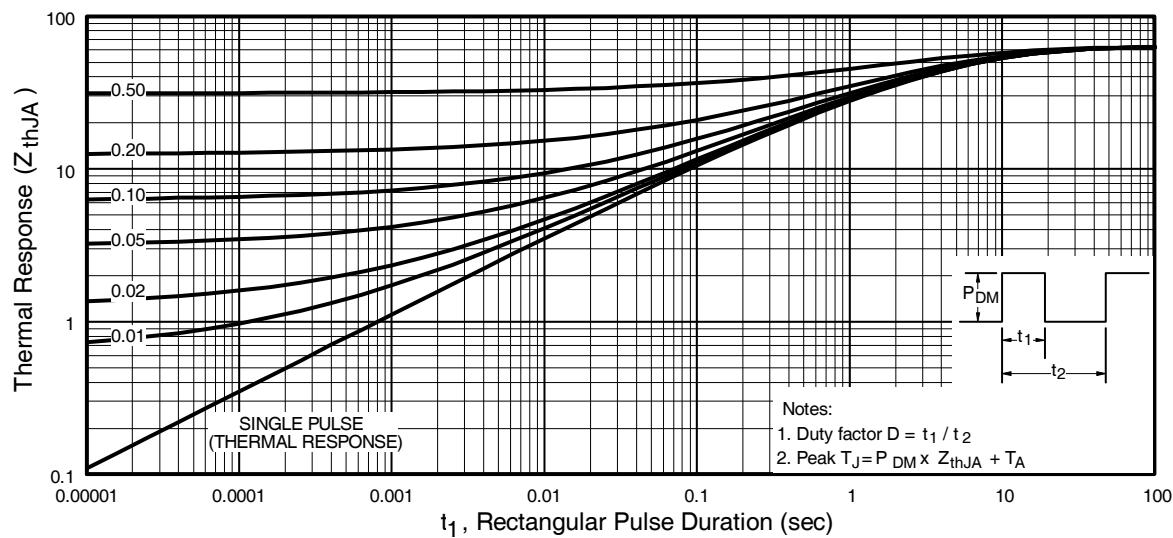
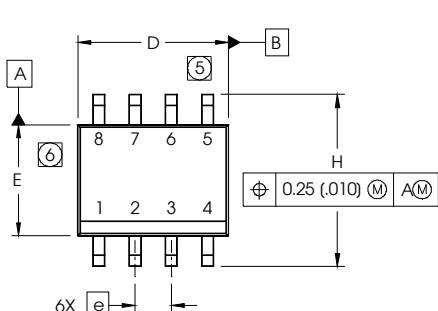


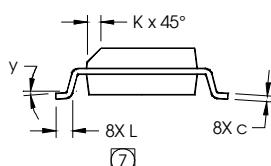
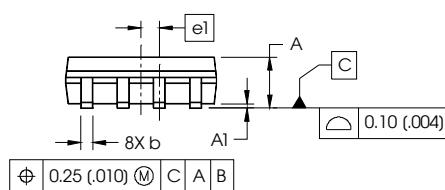
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

SO-8 Package Outline

Dimensions are shown in millimeters (inches)

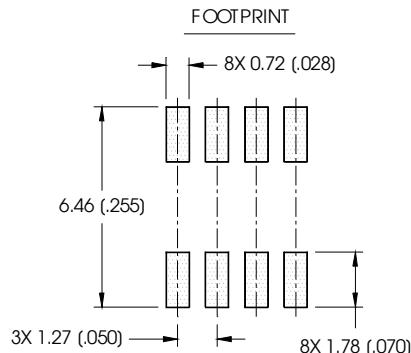


DIM	INCHES		MILLIMETERS	
	MN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050	BASIC	1.27	BASIC
e1	.025	BASIC	0.635	BASIC
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
Y	0°	8°	0°	8°

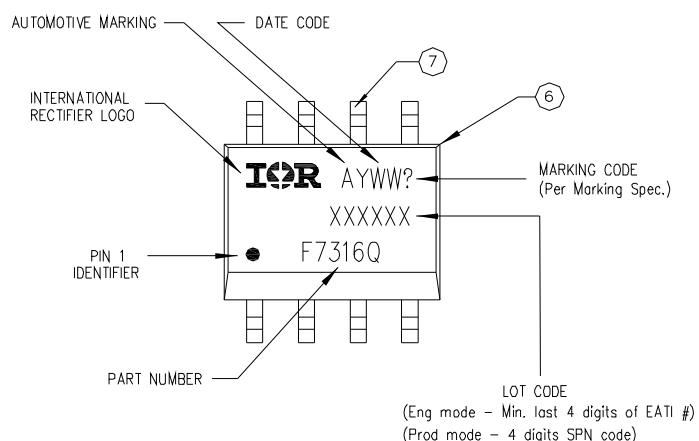


NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS.
MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS.
MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO
A SUBSTRATE.



SO-8 Part Marking

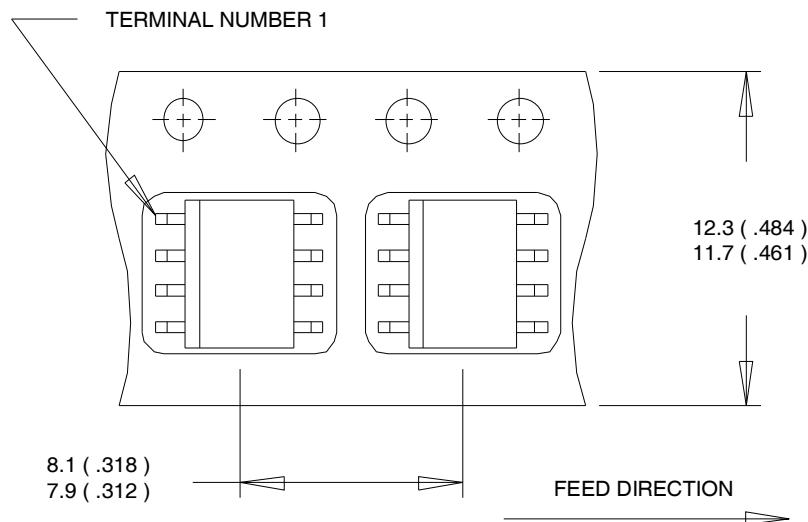


TOP MARKING (LASER)

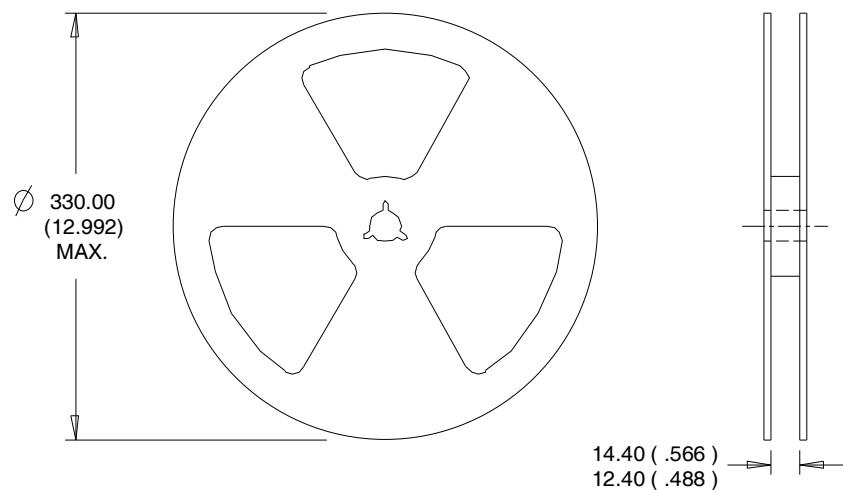
Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>
www.irf.com

SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)

**NOTES:**

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.

**NOTES :**

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Ordering Information

Base part	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRF7316Q	SO-8	Tube	95	AUIRF7316Q
		Tape and Reel	4000	AUIRF7316QTR

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<http://www.irf.com/technical-info/>

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